

2SK1862, 2SK1863

Silicon N-Channel MOS FET

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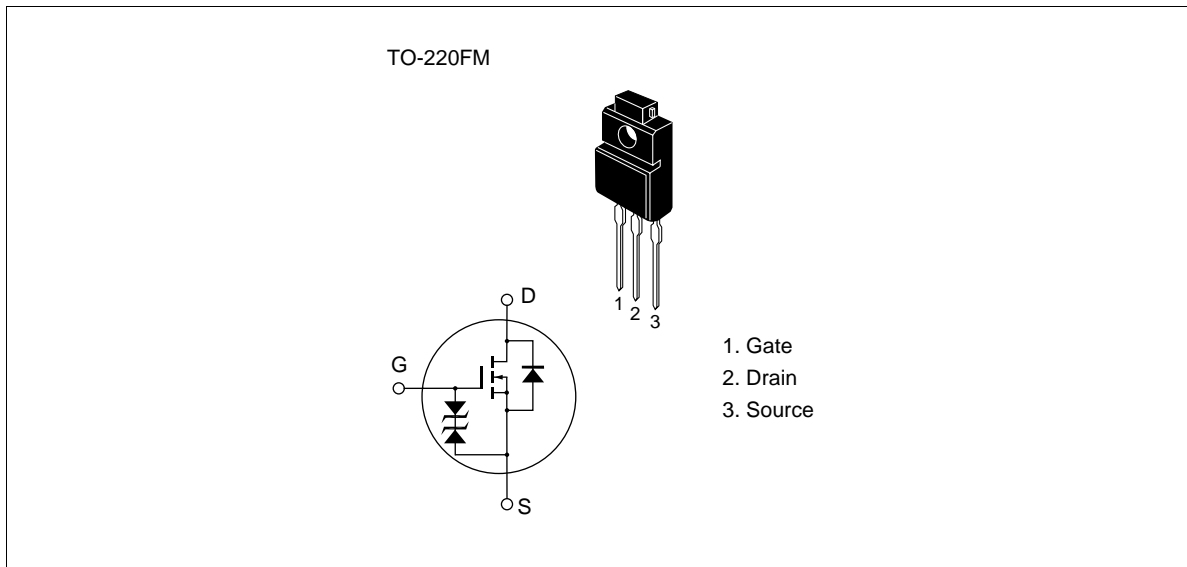
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for Switching regulator

Outline



2SK1862, 2SK1863

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1862	V_{DSS}	450	V
	2SK1863	V_{DSS}	500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	3	A
Drain peak current		$I_{D(pulse)}^{*1}$	12	A
Body to drain diode reverse drain current		I_{DR}	3	A
Channel dissipation		P_{ch}^{*2}	25	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ C$

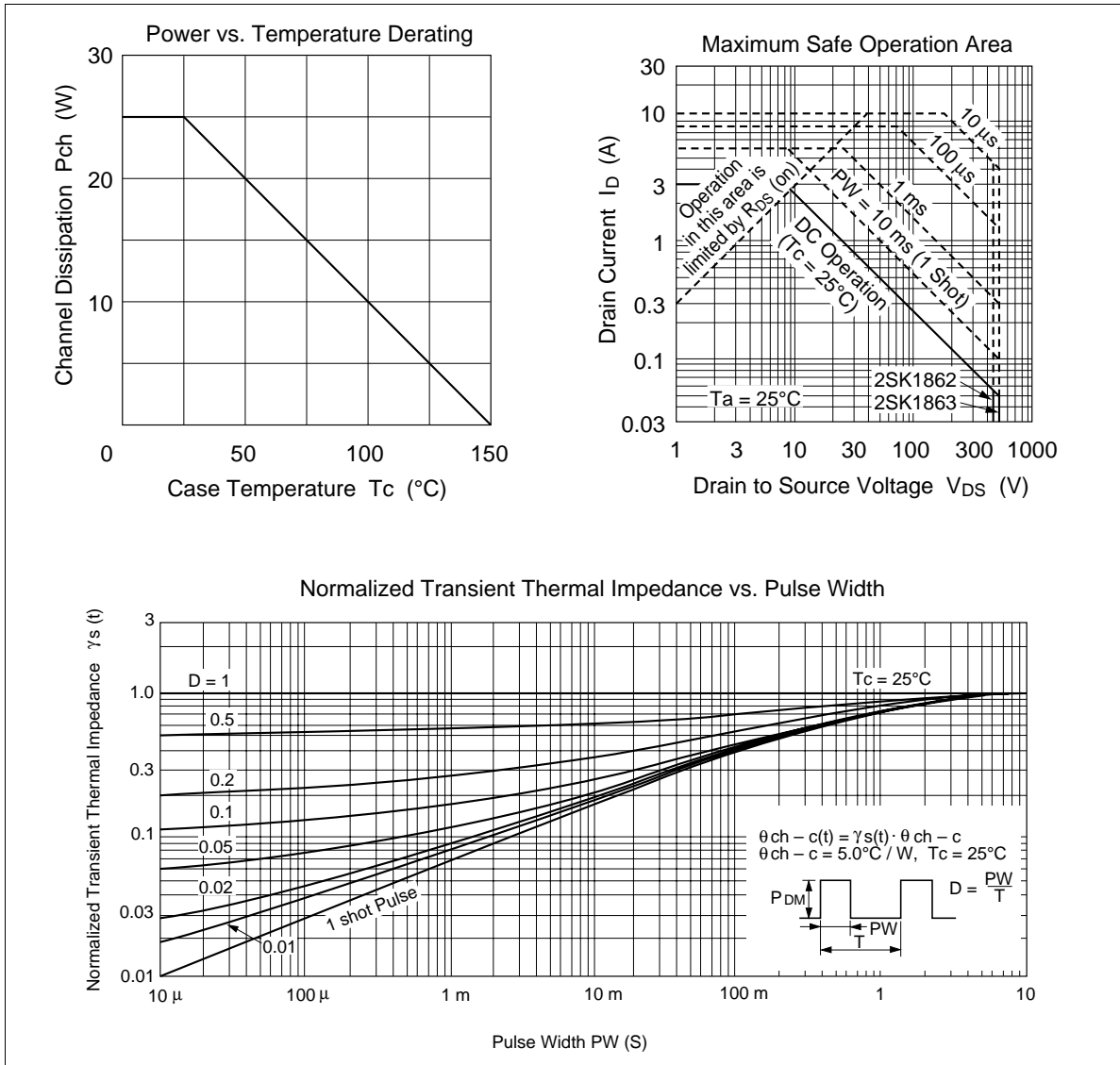
Electrical Characteristics (Ta = 25°C)

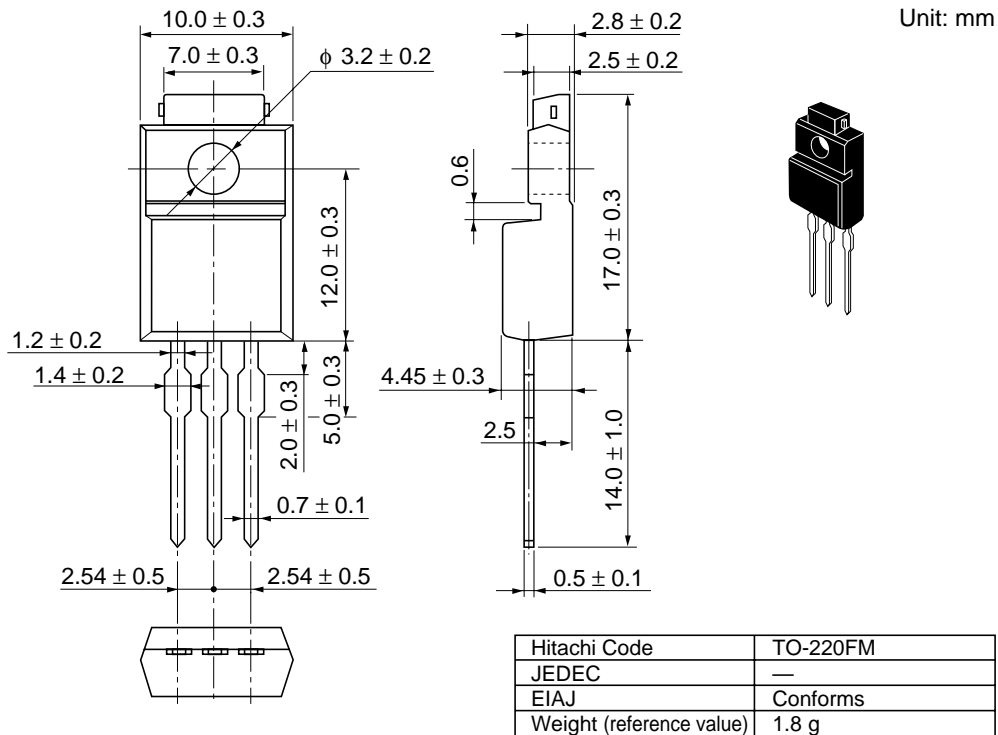
Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1862 2SK1863	$V_{(BR)DSS}$	450 500	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current		I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	2SK1862 2SK1863	I_{DSS}	—	—	250	μA	$V_{DS} = 360 \text{ V}, V_{GS} = 0$ $V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	2SK1862 2SK1863	$R_{DS(on)}$	—	2.0 2.2	2.8 3.0	Ω	$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance		$ y_{fs} $	1.5	2.5	—	S	$I_D = 2 \text{ A}$ $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		C_{iss}	—	330	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance		C_{oss}	—	90	—	pF	$V_{GS} = 0$
Reverse transfer capacitance		C_{rss}	—	15	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time		$t_{d(on)}$	—	7	—	ns	$I_D = 2 \text{ A}$
Rise time		t_r	—	20	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time		$t_{d(off)}$	—	30	—	ns	$R_L = 15 \Omega$
Fall time		t_f	—	20	—	ns	
Body to drain diode forward voltage		V_{DF}	—	0.9	—	V	$I_F = 3 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time		t_{rr}	—	300	—	ns	$I_F = 3 \text{ A}, V_{GS} = 0,$ $di_F / dt = 100 \text{ A} / \mu\text{s}$

Note 1. Pulse Test

See characteristic curves of 2SK1153, 2SK1154

2SK1862, 2SK1863





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